

## Additions and Corrections

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Sub-100-nm Pattern Formation through Selective Chemical Transformation of Self-Assembled Monolayers by Soft X-ray Irradiation

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On page 4395, in the last paragraph, the dosage required for the pattern fabrication is incorrect. The correct value is 1750 mJ/cm<sup>2</sup>. The wrong value originated from an incorrect estimation of the beam size. The fourth sentence of the last paragraph should be corrected as given below.

Dosage required for the pattern fabrication is 1750 mJ/cm<sup>2</sup>, and the sensitivity is lower than that of the octadecyltrichlorosilane system (optimum dosage: 1000 mJ/cm<sup>2</sup> at 1240 eV).<sup>23</sup>

LA0487085

10.1021/la0487085

Published on Web 07/02/2004